2N6107, 2N6109, 2N6111 (PNP), 2N6288, 2N6292 (NPN)

Complementary Silicon Plastic Power Transistors

These devices are designed for use in general-purpose amplifier and switching applications.

Features

- High DC Current Gain
- High Current Gain Bandwidth Product
- TO-220 Compact Package
- These Devices are Pb-Free and are RoHS Compliant*

MAXIMUM RATINGS (Note 1)

Rating	Symbol	Value	Unit
Collector–Emitter Voltage 2N6111, 2N6288 2N6109 2N6107, 2N6292	V _{CEO}	30 50 70	Vdc
Collector-Base Voltage 2N6111, 2N6288 2N6109 2N6107, 2N6292	V _{CB}	40 60 80	Vdc
Emitter-Base Voltage	V _{EB}	5.0	Vdc
Collector Current – Continuous	Ι _C	7.0	Adc
Collector Current – Peak	I _{CM}	10	Adc
Base Current	Ι _Β	3.0	Adc
Total Power Dissipation @ T _C = 25°C Derate above 25°C	P _D	40 0.32	W W/°C
Operating and Storage Junction Temperature Range	T _J , T _{stg}	-65 to +150	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. Indicates JEDEC Registered Data.

THERMAL CHARACTERISTICS

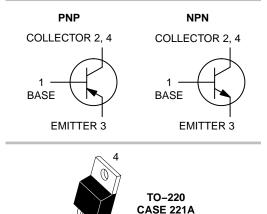
Characteristics	Symbol	Max	Unit
Thermal Resistance, Junction-to-Case	$R_{\theta JC}$	3.125	°C/W



ON Semiconductor®

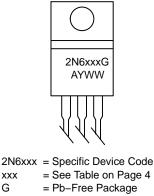
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7 AMPERE POWER TRANSISTORS COMPLEMENTARY SILICON 30 - 50 - 70 VOLTS, 40 WATTS



STYLE 1

MARKING DIAGRAM



ххх = Pb-Free Package

G = Assembly Location А

= Year Y

ww = Work Week

ORDERING INFORMATION See detailed ordering, marking, and shipping information in the package dimensions section on page 4 of this data sheet.

*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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2N6107, 2N6109, 2N6111 (PNP), 2N6288, 2N6292 (NPN)

ELECTRICAL CHARACTERISTICS ($T_C = 25^{\circ}C$ unless otherwise noted) (Note 2)
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Characteristic	Symbol	Min	Мах	Unit
OFF CHARACTERISTICS				
Collector–Emitter Sustaining Voltage (Note 3) (I _C = 100 mAdc, I _B = 0) 2N6111, 2N6288 2N6109 2N6107, 2N6292	V _{CEO(sus)}	30 50 70	- - -	Vdc
Collector Cutoff Current	I _{CEO}			mAdc
(V _{CE} = 20 Vdc, I _B = 0) 2N6111, 2N6288 (V _{CE} = 40 Vdc, I _B = 0)		-	1.0	
2N6109		-	1.0	
(V _{CE} = 60 Vdc, I _B = 0) 2N6107, 2N6292		-	1.0	
Collector Cutoff Current ($V_{CE} = 40 \text{ Vdc}, V_{EB(off)} = 1.5 \text{ Vdc}$)	ICEX		100	A -1-
2N6111, 2N6288 (V _{CE} = 60 Vdc, V _{EB(off)} = 1.5 Vdc)		-	100	μAdc
2N6109 (V _{CE} = 80 Vdc, V _{EB(off)} = 1.5 Vdc)		-	100	
2N6107, 2N6292 `´		-	100	
(V _{CE} = 30 Vdc, V _{EB(off)} = 1.5 Vdc, T _C = 150°C) 2N6111, 2N6288		-	2.0	mAdc
(V _{CE} = 50 Vdc, V _{EB(off)} = 1.5 Vdc, T _C = 150°C) 2N6109		-	2.0	
(V _{CE} = 70 Vdc, V _{EB(off)} = 1.5 Vdc, T _C = 150°C) 2N6107, 2N6292		-	2.0	
Emitter Cutoff Current ($V_{BE} = 5.0 \text{ Vdc}, I_{C} = 0$)	I _{EBO}	-	1.0	mAdc
DN CHARACTERISTICS (Note 3)	·			
	h _{FE}			-
(I _C = 2.0 Adc, V _{CE} = 4.0 Vdc) 2N6107, 2N6292		30	150	
(I _C = 2.5 Adc, V _{CE} = 4.0 Vdc) 2N6109		30	150	
(I _C = 3.0 Adc, V _{CE} = 4.0 Vdc) 2N6111, 2N6288		30	150	
$(I_C = 7.0 \text{ Adc}, V_{CE} = 4.0 \text{ Vdc})$ All Devices		2.3	_	
Collector–Emitter Saturation Voltage $(I_C = 7.0 \text{ Adc}, I_B = 3.0 \text{ Adc})$	V _{CE(sat)}	_	3.5	Vdc
Base–Emitter On Voltage (I _C = 7.0 Adc, V _{CE} = 4.0 Vdc)	V _{BE(on)}	_	3.0	Vdc
DYNAMIC CHARACTERISTICS				•
Current Gain – Bandwidth Product (Note 4) ($I_C = 500 \text{ mAdc}, V_{CE} = 4.0 \text{ Vdc}, f_{test} = 1.0 \text{ MHz}$)	f _T			MHz
2N6288, 2N6292 2N6107, 2N6109, 2N6111		4.0 10		
Dutput Capacitance (V _{CB} = 10 Vdc, I _E = 0, f = 1.0 MHz)	C _{ob}	_	250	pF
Small–Signal Current Gain	h _{fe}	20	_	-

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.
Indicates JEDEC Registered Data.
Pulse Test: Pulse Width ≤ 300 µs, Duty Cycle ≤ 2.0%.

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 $(I_{C} = 0.5 \text{ Adc}, V_{CE} = 4.0 \text{ Vdc}, f = 50 \text{ kHz})$

4. $f_T = |h_{fe}| \bullet f_{test}$

2N6107, 2N6109, 2N6111 (PNP), 2N6288, 2N6292 (NPN)

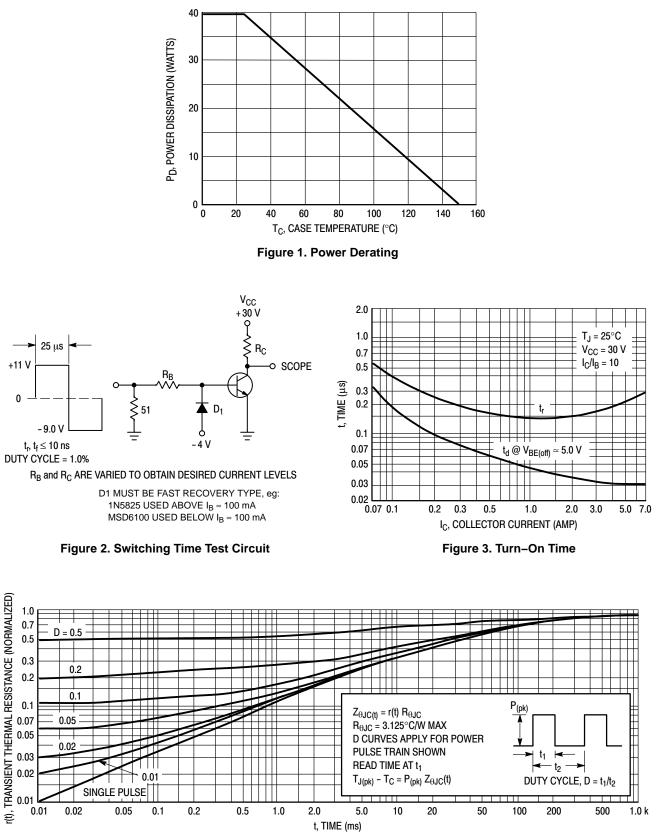


Figure 4. Thermal Response

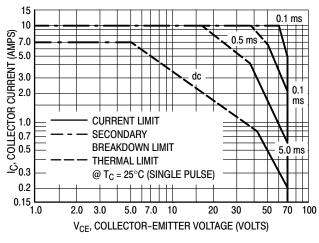
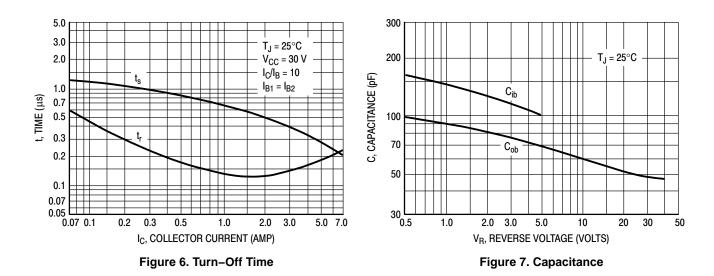


Figure 5. Active–Region Safe Operating Area

There are two limitations on the power handling ability of a transistor: average junction temperature and second breakdown. Safe operating area curves indicate I_C-V_{CE} limits of the transistor that must be observed for reliable operation; i.e., the transistor must not be subjected to greater dissipation than the curves indicate.

The data of Figure 5 is based on $T_{J(pk)} = 150^{\circ}C$; T_C is variable depending on conditions. Second breakdown pulse limits are valid for duty cycles to 10% provided $T_{J(pk)} \le 150^{\circ}C$. $T_{J(pk)}$ may be calculated from the data in Figure 4. At high case temperatures, thermal limitations will reduce the power that can be handled to values less than the limitations imposed by second breakdown.



ORDERING INFORMATION

Device	Device Marking	Package	Shipping
2N6107G	2N6107	TO-220 (Pb-Free)	50 Units / Rail
2N6109G	2N6109	TO–220 (Pb–Free)	50 Units / Rail
2N6111G	2N6111	TO–220 (Pb–Free)	50 Units / Rail
2N6288G	2N6288	TO–220 (Pb–Free)	50 Units / Rail
2N6292G	2N6292	TO–220 (Pb–Free)	50 Units / Rail

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		TO-220 CASE 221A ISSUE AK						DATE	13 JAN 2022
SCALE 1:1			1. C 2. C 3. C	CONTR DIMEN LEAD	ROLLING DI ISION Z DEI D IRREGULA	MENSION FINES A ZO ARITIES AR	ONE WHERE AL E ALLOWED.		
			4. N	лах м	VIDTHFOR	F102 DEV	ICE = 1.35MM		
			Г		INC	HES	MILLIM	ETERS	
				ым 🛛	MIN.	MAX.	MIN.	MAX.	
	2 3			A	0.570	0.620	14.48	15.75	
				в	0.380	0.415	9.66	10.53	
н —	₩₩			с	0.160	0.190	4.07	4.83	
	7 \7	H I		D	0.025	0.038	0.64	0.96	
z_				F	0.142	0.161	3.60	4.09	
<u> </u>	I K			G	0.095	0.105	2.42	2.66	
				н	0.110	0.161	2.80	4.10	
	Щ Щ <u> </u>	Ü I		J	0.014	0.024	0.36	0.61	
	Г <mark>і</mark>			к	0.500	0.562	12.70	14.27	
V — + I I-	►- ``.			L	0.045	0.060	1.15	1.52	
G 	. <mark> </mark> J [−]			N	0.190	0.210	4.83	5.33	
· · · ·	- → D			Q	0.100	0.120	2.54	3.04	
	N 🖛			R	0.080	0.110	2.04	2.79	
				s	0.045	0.055	1.15	1.41	
				т	0.235	0.255	5.97	6.47	
				U	0.000	0.050	0.00	1.27	
				V	0.045		1.15		
				Z		0.080		2.04	
2. 3. 4. STYLE 5: PIN 1. 2.	BASE PIN 1. COLLECTOR 2. EMITTER 3. COLLECTOR 4. STYLE 6: GATE DRAIN 2.	EMITTER COLLECTOR EMITTER ANODE CATHODE	IN 1. CAT 2. ANO 3. GAT 4. ANO LE 7: IN 1. CAT 2. ANO	ode Te ode Thode ode		2. 3. 4. STYLE 8: PIN 1. 2.	MAIN TERMINAL MAIN TERMINAL GATE MAIN TERMINAL CATHODE ANODE	2	
4. STYLE 9: PIN 1.	DRAIN 4. STYLE 10 GATE PIN 1.	ANODE CATHODE GATE P SOURCE	3. CAT 4. ANO LE 11: IN 1. DR/ 2. SOU	ode Ain		4. STYLE 12: PIN 1.	EXTERNAL TRIP ANODE MAIN TERMINAL MAIN TERMINAL	. 1	
3.	EMITTER 3.	DRAIN SOURCE	3. GAT 4. SOL	ΤE		3.	GATE NOT CONNECTI		

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